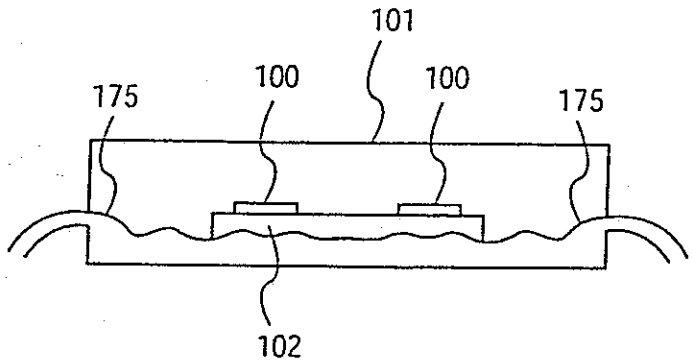


FIG. 1

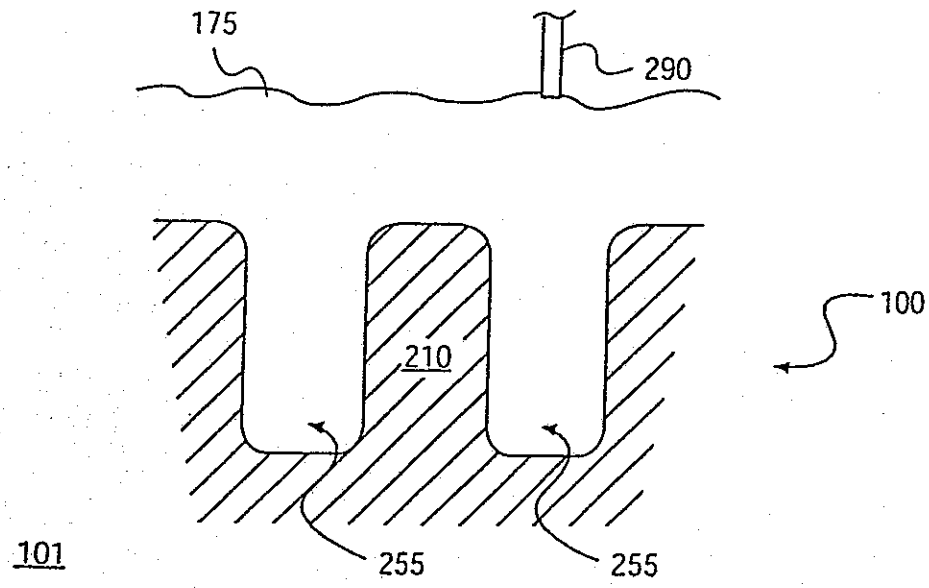


FIG. 2

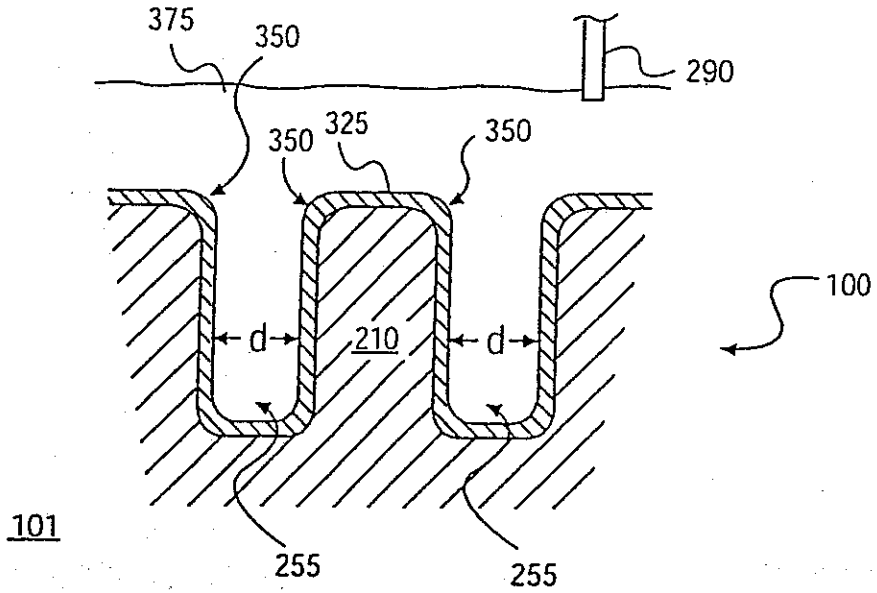

375
350
290
350
325
350
100
d
210
d
101
255
255

FIG. 3

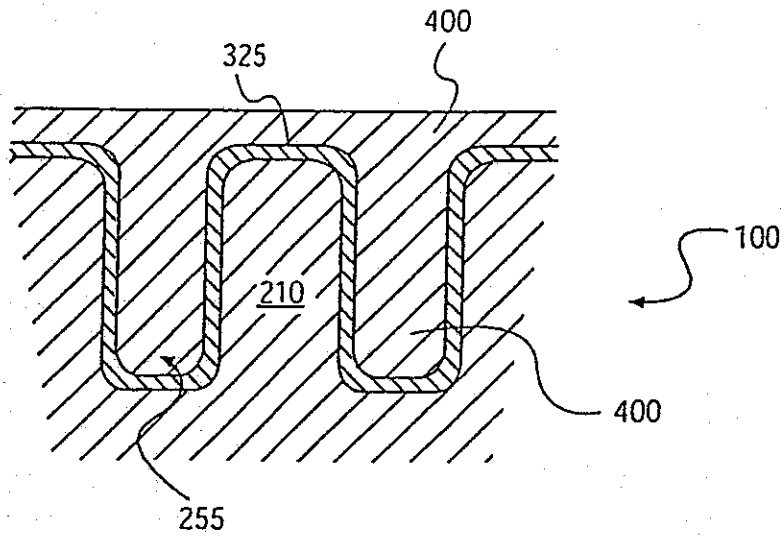

400
325
100
210
400
255

FIG. 4

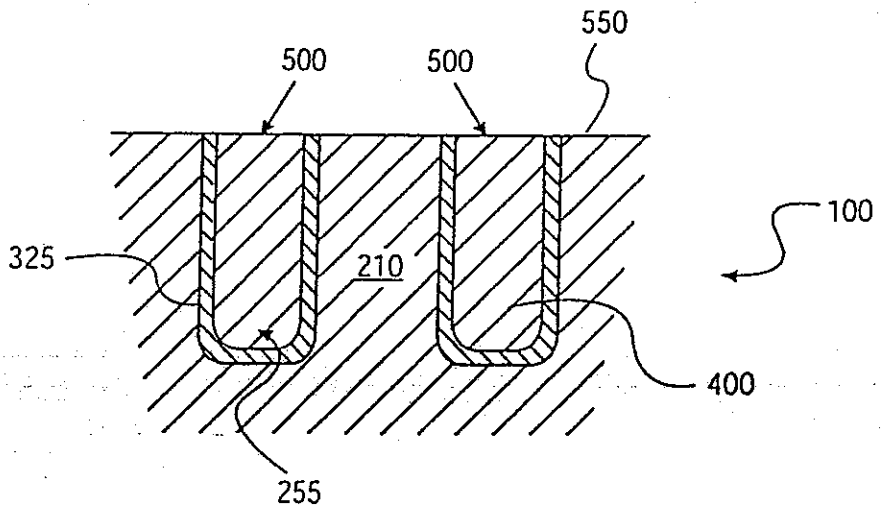


FIG. 5

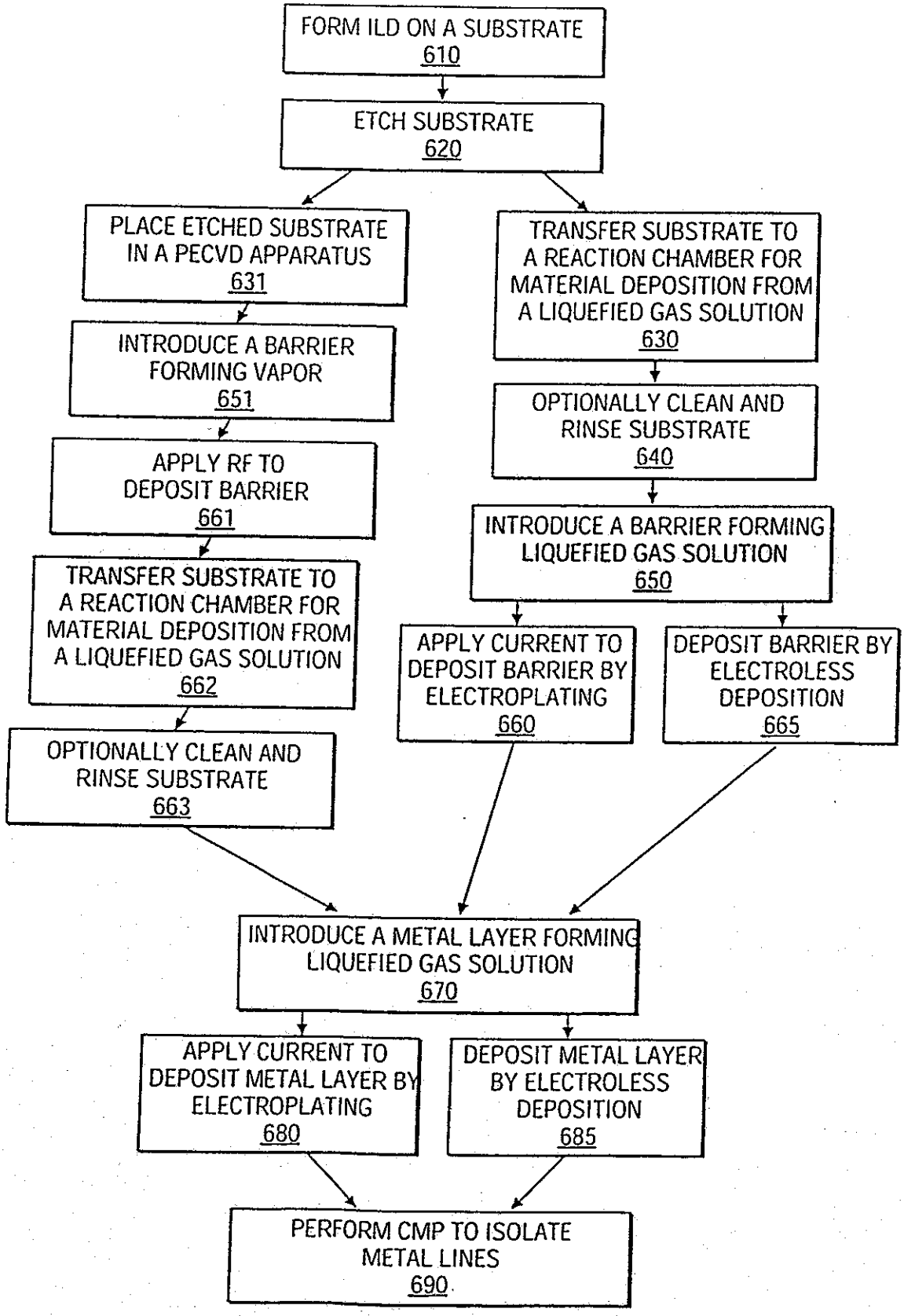

FORM ILD ON A SUBSTRATE
610
ETCH SUBSTRATE
620
PLACE ETCHED SUBSTRATE IN A PECVD APPARATUS
631
INTRODUCE A BARRIER FORMING VAPOR
651
APPLY RF TO DEPOSIT BARRIER
661
TRANSFER SUBSTRATE TO A REACTION CHAMBER FOR MATERIAL DEPOSITION FROM A LIQUEFIED GAS SOLUTION
662
OPTIONALLY CLEAN AND RINSE SUBSTRATE
663
TRANSFER SUBSTRATE TO A REACTION CHAMBER FOR MATERIAL DEPOSITION FROM A LIQUEFIED GAS SOLUTION
630
OPTIONALLY CLEAN AND RINSE SUBSTRATE
640
INTRODUCE A BARRIER FORMING LIQUEFIED GAS SOLUTION
650
APPLY CURRENT TO DEPOSIT BARRIER BY ELECTROPLATING
660
DEPOSIT BARRIER BY ELECTROLESS DEPOSITION
665
INTRODUCE A METAL LAYER FORMING LIQUEFIED GAS SOLUTION
670
APPLY CURRENT TO DEPOSIT METAL LAYER BY ELECTROPLATING
680
DEPOSIT METAL LAYER BY ELECTROLESS DEPOSITION
685
PERFORM CMP TO ISOLATE METAL LINES
690

FIG. 6